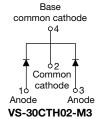
**Vishay Semiconductors** 

# Hyperfast Rectifier, 2 x 15 FRED Pt<sup>®</sup>



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PRIMARY CHARACTERISTICS					
V <sub>R</sub>	200 V				
V <sub>F</sub> at I <sub>F</sub>	0.78 V				
t <sub>rr</sub> typ.	See Recovery table				
T <sub>J</sub> max.	175 °C				
Package	3L TO-220AB				
I <sub>F(AV)</sub>	2 x 15 A				
Circuit configuration	Common cathode				

### FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V			
Average rectified forward current	per diode		T <sub>C</sub> = 159 °C	15				
Average rectilied forward current	per device	IF(AV)		30	А			
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	200				
Operating junction and storage temperate	ures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-			
		I <sub>F</sub> = 15 A	-	0.92	1.05	V		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C	-	0.78	0.85			
Reverse leakage current	1	$V_{R} = V_{R}$ rated	-	-	10			
neverse leakage current	I <sub>R</sub>	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	5	300	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	57	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH		

Revision: 26-Oct-17 1 Document Number: 96206 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_C = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50$	A/µs, V <sub>R</sub> = 30 V	-	-	35			
Povorco rocovoru timo	+	I <sub>F</sub> = 1 A, dI <sub>F</sub> /dt = 100 A/µs, V <sub>R</sub> = 30 V		-	-	30	ns		
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 160 V	-	26	-	115		
		T <sub>J</sub> = 125 °C		-	40	-			
Peak recovery current		T <sub>J</sub> = 25 °C		-	2.8	-	А		
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C		-	6.0	-			
	0	T <sub>J</sub> = 25 °C		-	37	-	nC		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-			

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNIT								
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C		
Thermal resistance, junction-to-case per diode	R <sub>thJC</sub>	Mounting surface, flat, smooth and greased	-	-	1.1	°C/W		
Marking device		Case style 3L TO-220AB	30CTH02					

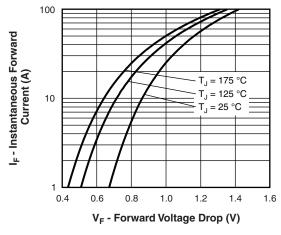


Fig. 1 - Typical Forward Voltage Drop Characteristics

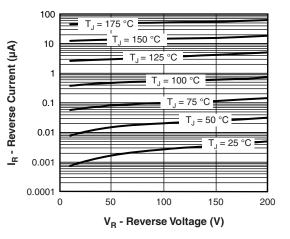


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

## VS-30CTH02-M3

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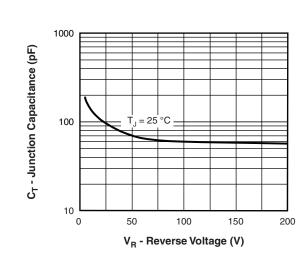


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

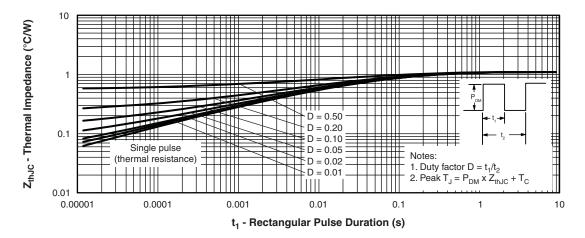
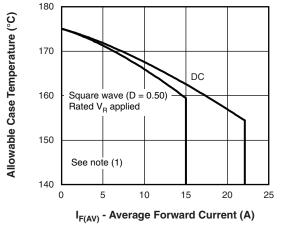
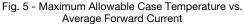


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5);} \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_{R} (1 - D); I_{R} \text{ at } V_{R1} = \text{rated } V_{R} \end{array}$ 

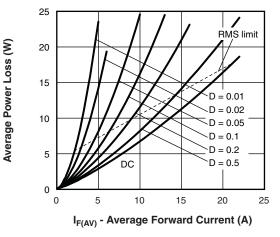


Fig. 6 - Forward Power Loss Characteristics

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# VS-30CTH02-M3

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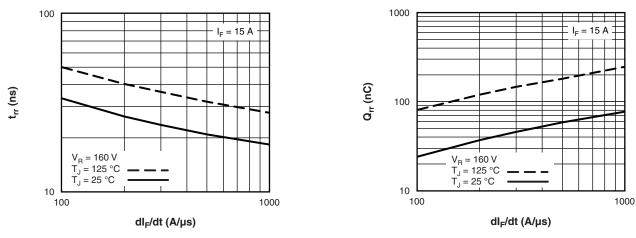


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

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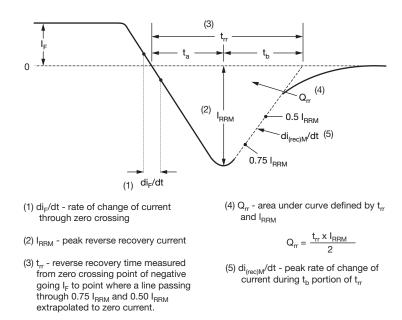


Fig. 9 - Reverse Recovery Waveform and Definitions





### **ORDERING INFORMATION TABLE**

Device code	VS-	30	с	т	н	02	-M3
		2	3	4	5	6	7
	1 .	· Visł	nay Sem	iconduc	ctors pro	oduct	
	2 -		rent rati	0.	,		
	3 .	-	commo		de		
	4 -	-	TO-220				
	5 -	• H=	hyperfa	st reco	/ery		
	6	· Volt	age rati	ng (02 =	= 200 V)		
	7 -		ironmer	0			
		-M3	s = halog	gen-free	, RoHS	-compli	ant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-30CTH02-M3	50	1000	Antistatic plastic tube				

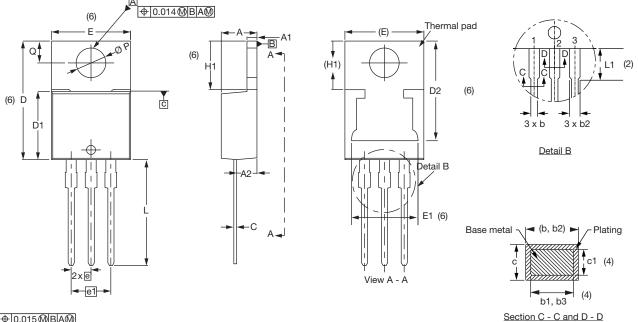
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96154					
Part marking information	www.vishay.com/doc?95028				



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## **3L TO-220AB**

### **DIMENSIONS** in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	NOTES	
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

_		
Conforms to JEDEC <sup>®</sup>	outline	<b>TO-220AB</b>

SYMBOL	MILLIN	IETERS	INC	NOTES	
STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

#### Notes

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

- <sup>(4)</sup> Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2, and E1
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2

Revision: 13-Jun-2019

 $<sup>^{(1)}\,</sup>$  Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(3)</sup> Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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